Dual N-channel Enhancement Mode Power MOSFET

Features

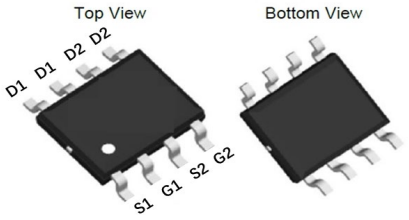
- VDS= 20V, ID= 10 A
  RDS(ON) < 9 mΩ @ VGS = 10V
  RDS(ON) < 12 mΩ @ VGS = 4.5V

General Features

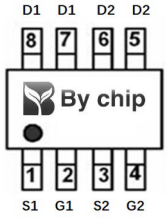
- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead Free and Green Available

100% UIS TESTED!
100% ΔVds TESTED!

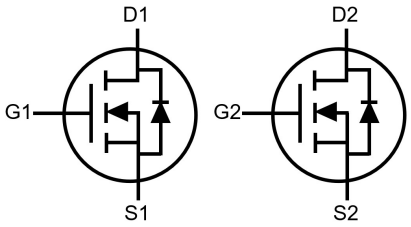
RoHS



SOP-8 (Dual)



Pin Assignment



Schematic diagram

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	10[a]	A
	T_C = 70 °C		7.0	
	T_A = 25 °C		8.1[b, c]	
	T_A = 70 °C		7.2[b, c]	
Pulsed Drain Current		I_{DM}	44	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	3.25	
	T_A = 25 °C		1.88[b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	6	
Single Pulse Avalanche Energy		E_{AS}	1.45	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	2.7	W
	T_C = 70 °C		1.77	
	T_A = 25 °C		1.78[b, c]	
	T_A = 70 °C		1.14[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

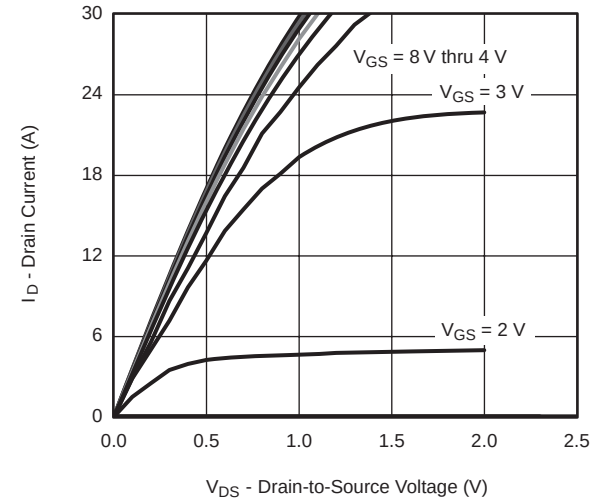
THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a, c, d]	t ≤ 10 s	R_{thJA}	58	70	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	38	45	

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		32		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.0		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 250 µA	0.5		1.0	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 4.5 V	10			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 5 A		0.009		Ω
		V_{GS} = 2.5 V, I_D = 4 A		0.012		
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 5 A		16		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 10V, V_{GS} = 0 V, f = 1 MHz		586		pF
Output Capacitance	C_{oss}			117		
Reverse Transfer Capacitance	C_{rss}			55		
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 10 V, I_D = 5 A		15		nC
		V_{DS} = 10V , V_{GS} = 4.5 V, I_D = 5 A		3.7	5.6	
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			1.05		
Gate Resistance	R_g	f = 1 MHz	0.8	4.3	8.6	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 3 Ω $I_D \cong$ 5 A, V_{GEN} = 4.5 V, R_g = 1 Ω		12	24	ns
Rise Time	t_r			55	100	
Turn-Off Delay Time	$t_{d(off)}$			11	22	
Fall Time	t_f			8	16	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10V, R_L = 3 Ω $I_D \cong$ 5 A, V_{GEN} = 10 V, R_g = 1 Ω		4	8	
Rise Time	t_r			9	18	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			6	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			2.35	A
Pulse Diode Forward Current	I_{SM}				24	
Body Diode Voltage	V_{SD}	I_S = 2 A, V_{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 5 A, dI/dt = 100 A/µs, T_J = 25 °C		11	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}			4	8	nC
Reverse Recovery Fall Time	t_a			7		ns
Reverse Recovery Rise Time	t_b			4		

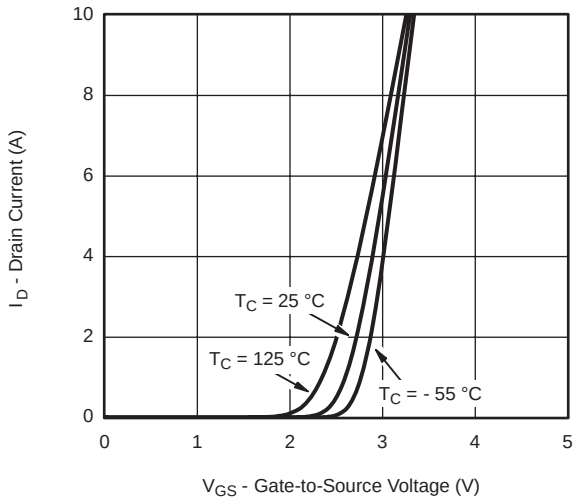
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

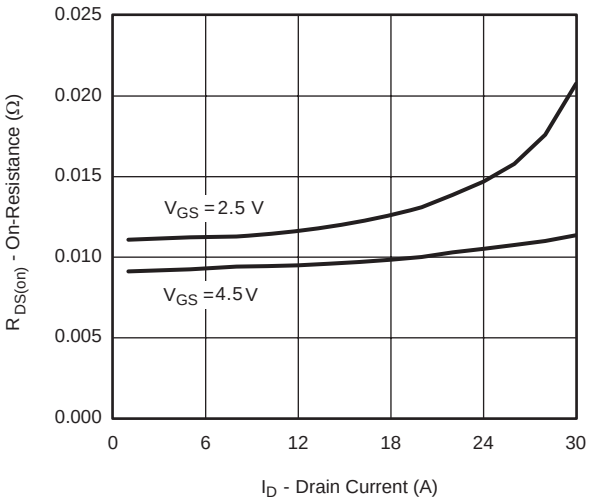
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



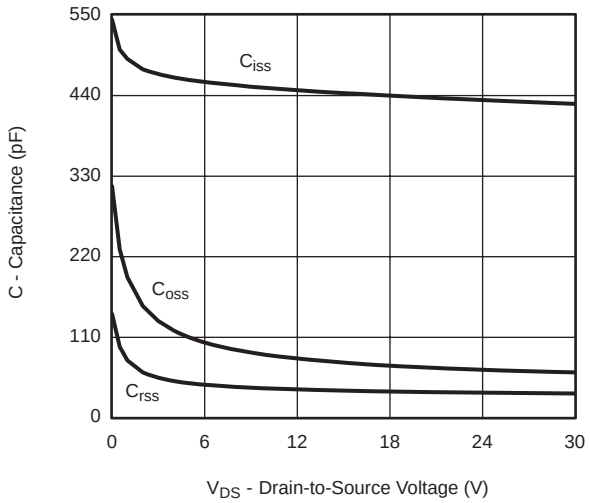
Output Characteristics



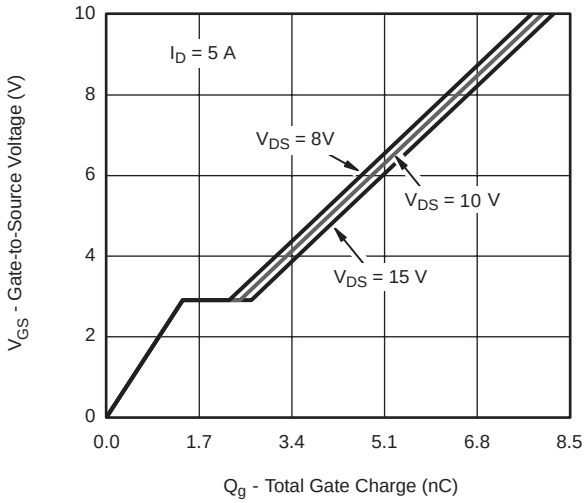
Transfer Characteristics



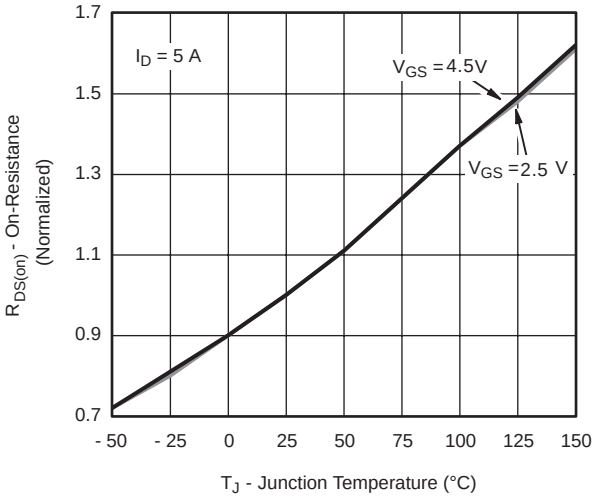
On-Resistance vs. Drain Current



Capacitance

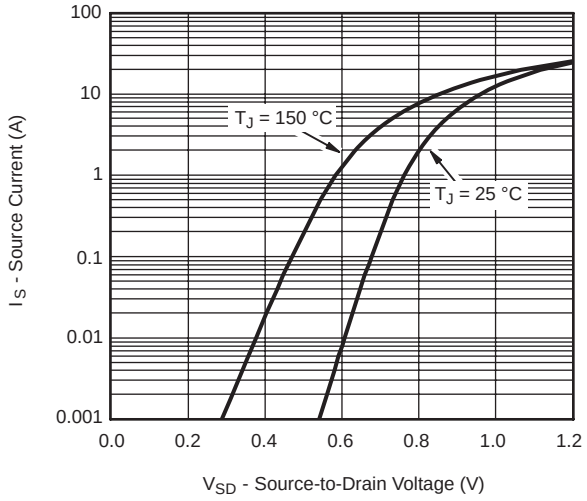


Gate Charge

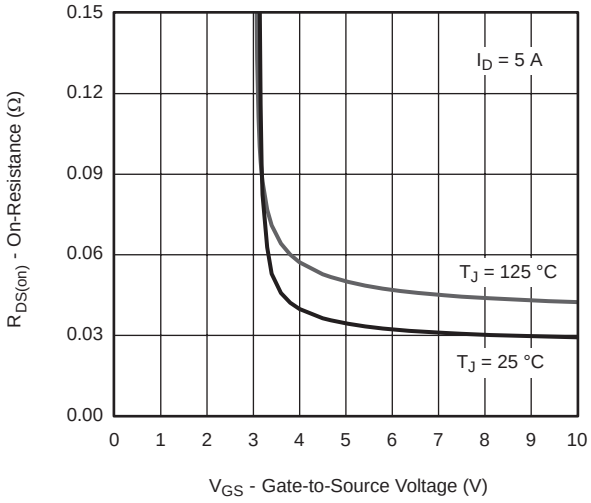


On-Resistance vs. Junction Temperature

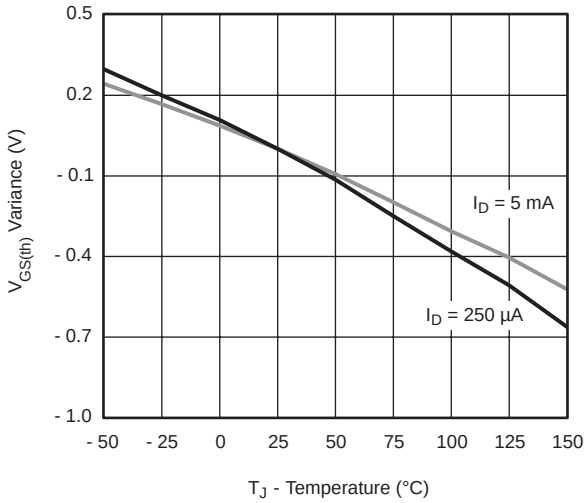
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



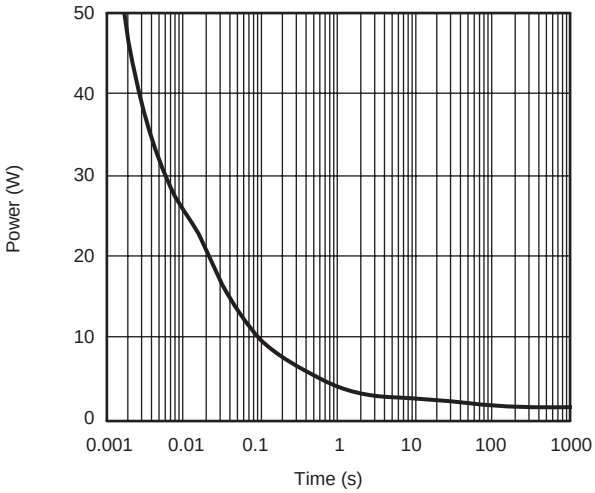
Source-Drain Diode Forward Voltage



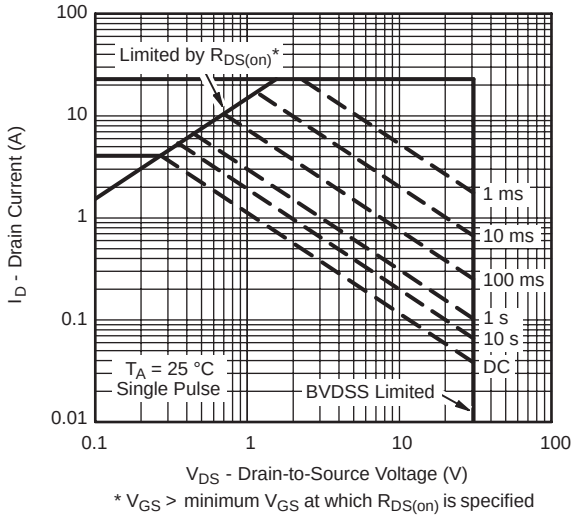
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

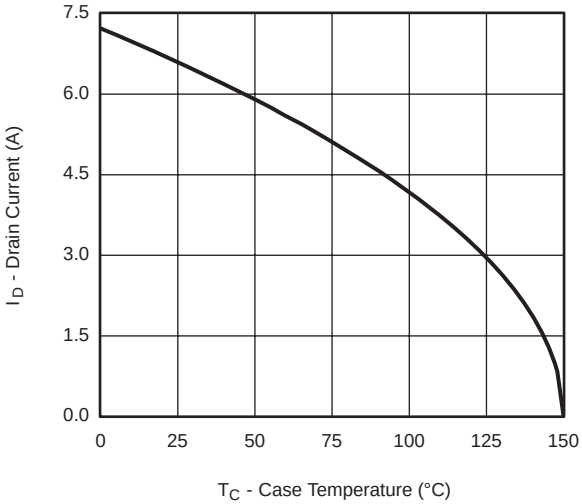


Single Pulse Power



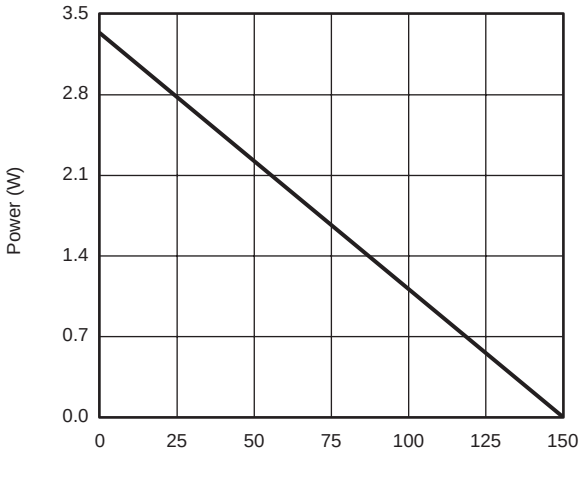
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

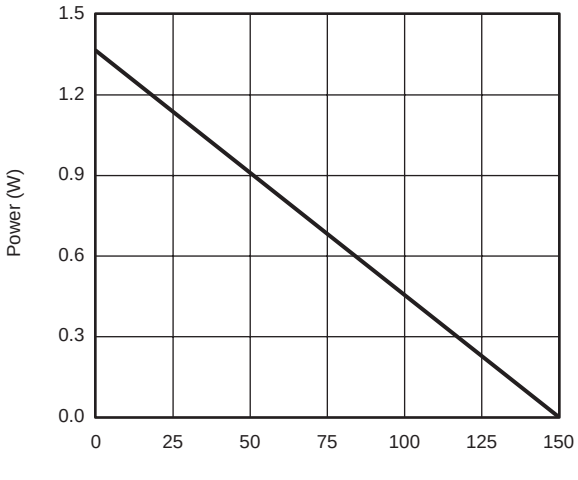


Current Derating*

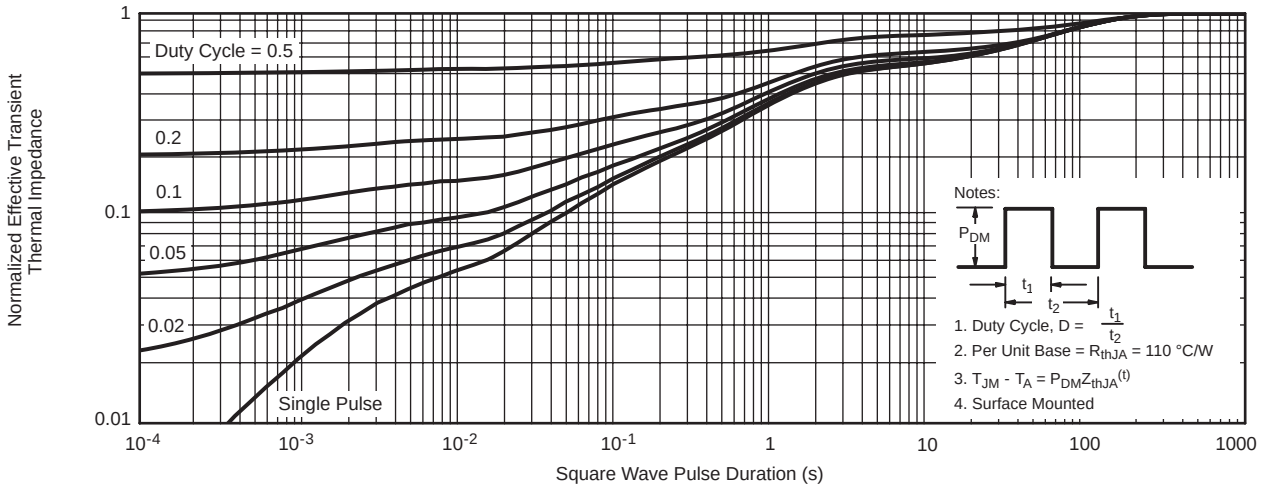
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



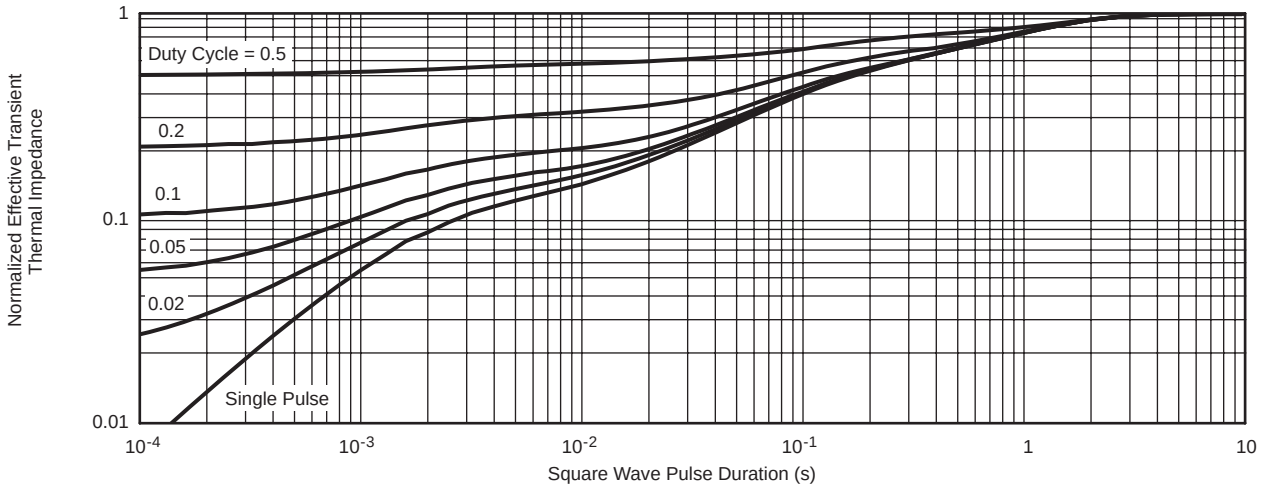
Power, Junction-to-Foot



Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot